

			10/04	Time stamp
1	4148	(257/173,355.ccls.: 361/90,91,91.1-91.8,FOR100.ccls.)	USPA1; US-PGPUB; 2004/08/17	EPO; JPO; 15:39
2	213	esd with buried	DERWENT; IBM_TDB	
3	44	((257/173,355.ccls.: 361/90,91,91.1-91.8,FOR100.ccls.) and (esd with buried))	USPA1; US-PGPUB; 2004/08/17	EPO; JPO; 12:05
4	28	((257/173,355.ccls.: 361/90,91,91.1-91.8,FOR100.ccls.) and (esd with buried) and pad)	DERWENT; IBM_TDB	
5	16	((257/173,355.ccls.: 361/90,91,91.1-91.8,FOR100.ccls.) and (esd with buried)) not ((257/173,355.ccls.: 361/90,91,91.1-91.8,FOR100.ccls.) and (esd with buried) and pad)	USPA1; US-PGPUB; 2004/08/17	EPO; JPO; 12:13
6	319	esd same ((under or below) with pad)	DERWENT; IBM_TDB	
7	95	(esd same ((under or below) with pad)) and (257/173,355.ccls.: 361/90,91,91.1-91.8,FOR100.ccls.)	USPA1; US-PGPUB; 2004/08/17	EPO; JPO; 12:20
8	83	((esd same ((under or below) with pad)) and (257/173,355.ccls.: 361/90,91,91.1-91.8,FOR100.ccls.)) not ((257/173,355.ccls.: 361/90,91,91.1-91.8,FOR100.ccls.)) and (esd with buried) and pad)	DERWENT; IBM_TDB	
9	41456	vias with resistance	USPA1; US-PGPUB; 2004/08/17	EPO; JPO; 14:59
10	1857	vias with resistance with parallel	DERWENT; IBM_TDB	
11	258	esd and (resistance or resistor) and (transistor same below same pad)	USPA1; US-PGPUB; 2004/08/17	EPO; JPO; 15:39
12	4148	(257/173,355.ccls.: 361/90,91,91.1-91.8,FOR100.ccls.)	DERWENT; IBM_TDB	
13	56	(esd and (resistance or resistor) and (transistor same below same pad)) and (257/173,355.ccls.: 361/90,91,91.1-91.8,FOR100.ccls.))	USPA1; US-PGPUB; 2004/08/17	EPO; JPO; 15:39
			DERWENT; IBM_TDB	

EAST 8/17/04